

General Description

The AO4852 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. As a pair these MOSFETs operate very efficiently in Push Pull and Bridge topologies.

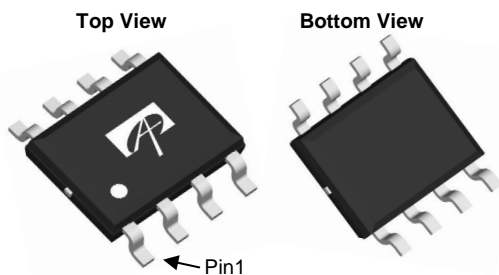
Product Summary

V_{DS} (V) = 60V
 I_D = 3.5A (V_{GS} = 10V)
 $R_{DS(ON)}$ < 90m Ω (V_{GS} = 10V)
 $R_{DS(ON)}$ < 105m Ω (V_{GS} = 4.5V)

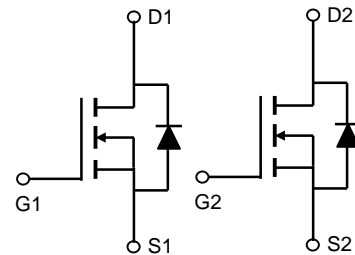
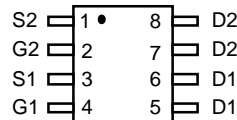
100% UIS Tested
 100% Rg Tested



SOIC-8



Top View



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum		Units
		10 Sec	Steady State	
Drain-Source Voltage	V_{DS}	60		V
Gate-Source Voltage	V_{GS}	± 20		V
Continuous Drain Current ^A	$T_A=25^\circ\text{C}$	3.5	3	A
	$T_A=70^\circ\text{C}$	2.8	2.4	
Pulsed Drain Current ^B	I_{DM}	20		
Power Dissipation	$T_A=25^\circ\text{C}$	2	1.4	W
	$T_A=70^\circ\text{C}$	1.3	0.9	
Avalanche Current ^B	I_{AR}	8		A
Repetitive avalanche energy 0.3mH ^B	E_{AR}	9.6		mJ
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A $t \leq 10\text{s}$	$R_{\theta JA}$	48	62.5	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient ^A Steady-State		74	90	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Lead ^C Steady-State	$R_{\theta JL}$	33	40	$^\circ\text{C}/\text{W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
B _V DSS	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	1.7	2.3	2.6	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	20			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =3A T _J =125°C		79 146	90 159	mΩ
		V _{GS} =4.5V, I _D =2A		86	105	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =3A		15		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.8	1	V
I _{SM}	Pulsed Body-Diode Current ^B				20	A
I _S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, f=1MHz		372	450	pF
C _{oss}	Output Capacitance			31		pF
C _{rss}	Reverse Transfer Capacitance			17		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		1.7	2.6	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =30V, I _D =3A		7.1	9.2	nC
Q _g (4.5V)	Total Gate Charge			3.6		nC
Q _{gs}	Gate Source Charge			1		nC
Q _{gd}	Gate Drain Charge			2		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =30V, R _L =10Ω, R _{GEN} =3Ω		4.1	5.3	ns
t _r	Turn-On Rise Time			2.1		ns
t _{D(off)}	Turn-Off DelayTime			15		ns
t _f	Turn-Off Fall Time			2.1		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =3A, di/dt=100A/μs		23.4	29	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =3A, di/dt=100A/μs		23.2		nC

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using < 300 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

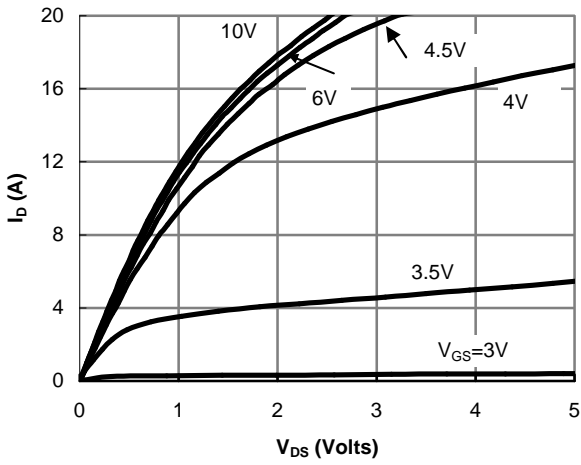


Fig 1: On-Region Characteristics

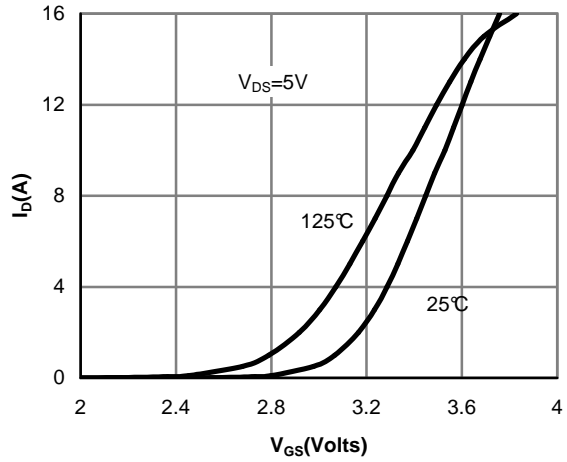


Figure 2: Transfer Characteristics

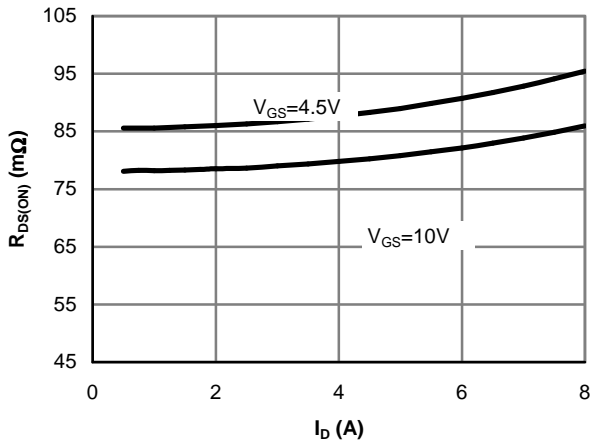


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

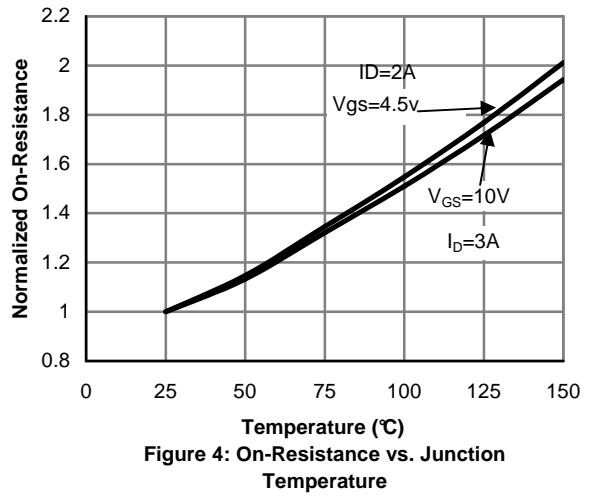


Figure 4: On-Resistance vs. Junction Temperature

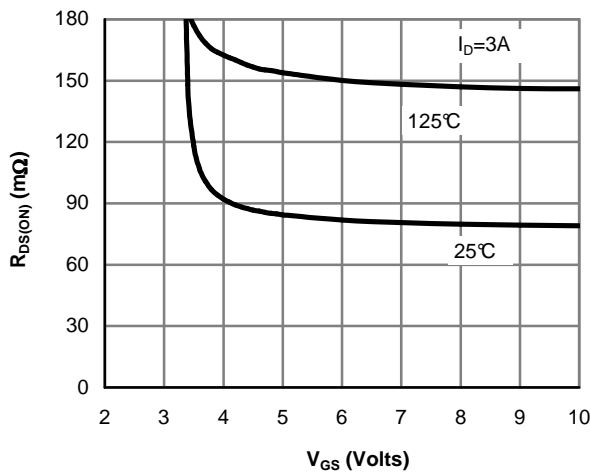


Figure 5: On-Resistance vs. Gate-Source Voltage

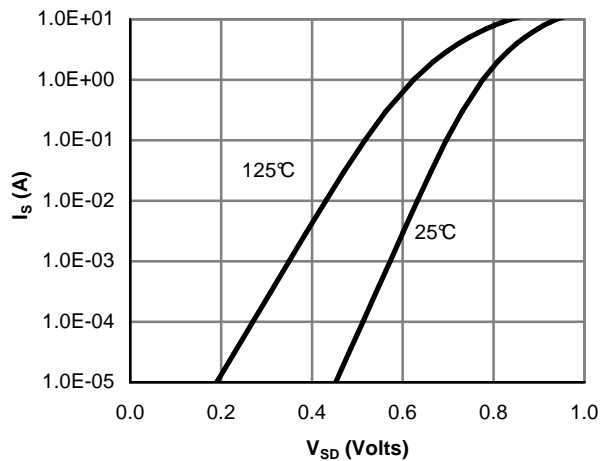


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

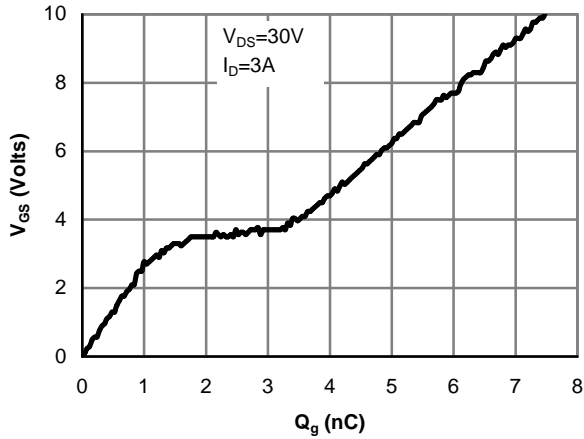


Figure 7: Gate-Charge Characteristics

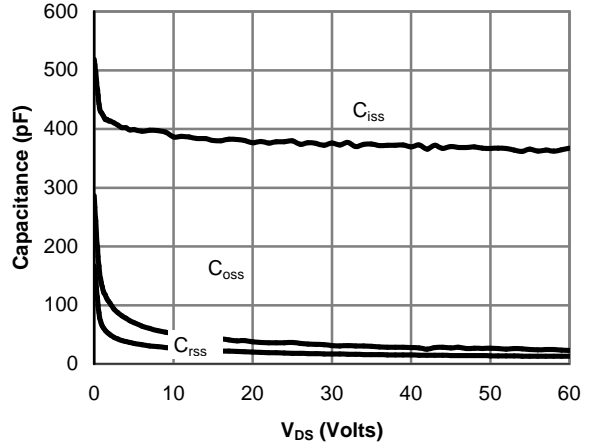


Figure 8: Capacitance Characteristics

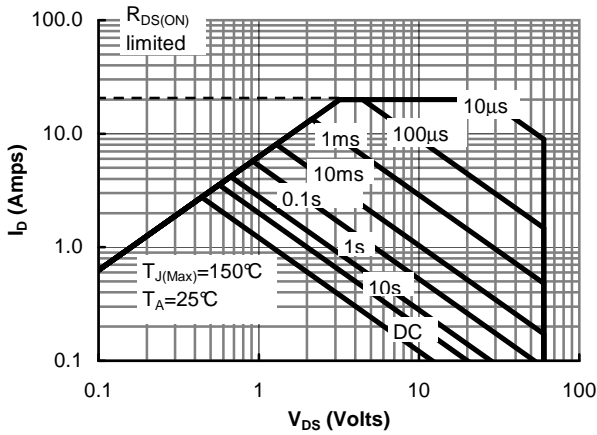


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

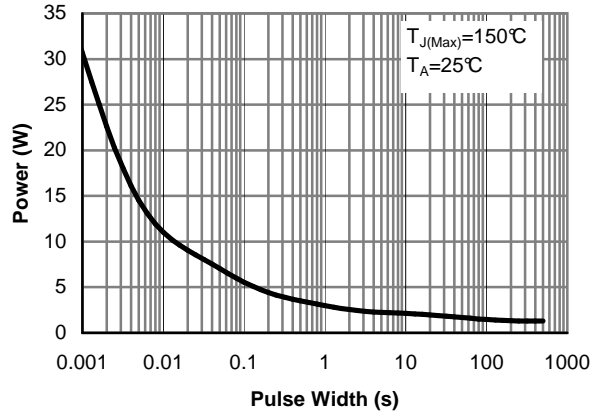


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

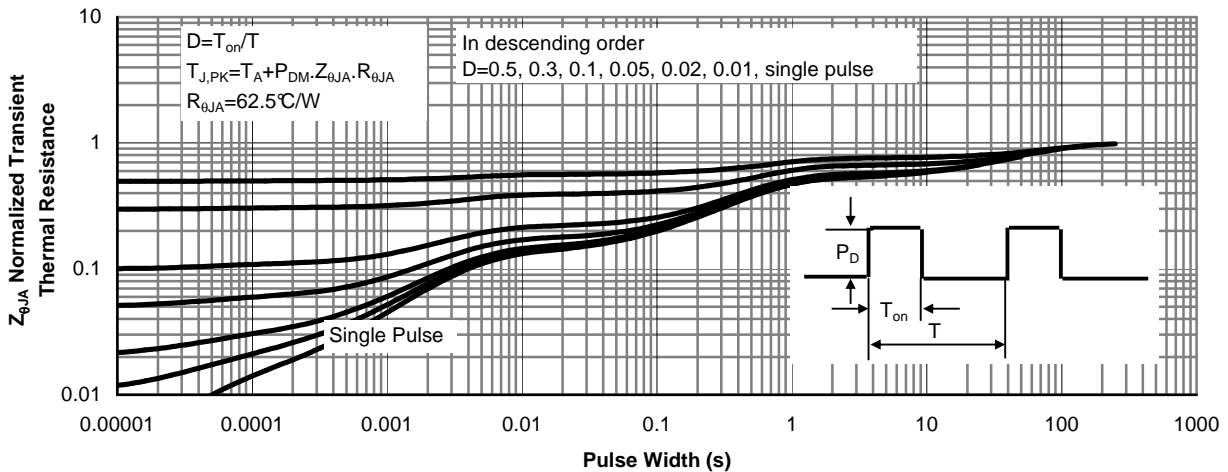


Figure 11: Normalized Maximum Transient Thermal Impedance